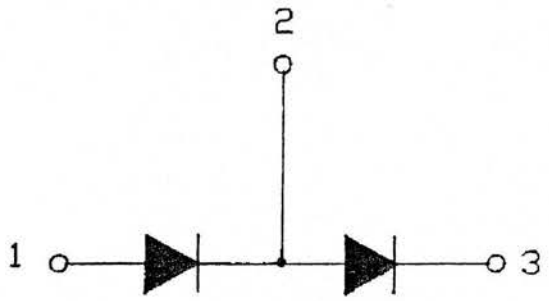
# MA/COM MA4E501



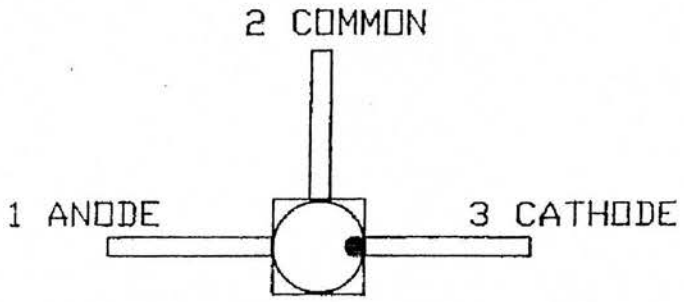




**TABLE 1**

| N° | CHARACTERISTICS | SYMB | LIMIT | UNIT | REMARKS |
|---|---|---|---|---|---|
| 1 | Reverse Voltage | $V_R$ | 3 min. | V | $I_R$ = 10 µA |
| 2 | Power Dissipation | $P_D$ | 55 | mW | For junction |
| 3 | Operating Temperature | $T_{OP}$ | -65÷+150 | °C | |
| 4 | Soldering Temperature | $T_{SOL}$ | 235 | °C | For 10 sec. |
| 5 | Storage Temperature | $T_{ST}$ | -65÷+150 | °C | |

**TABLE 2**

| Nr | CHARACTERISTICS | SYMB | MIL STD-750 | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| 1 | Breakdown Voltage | $V_{BR}$ | 4021 | $I_R$ = 10 µA | 3 | | | V |
| 2 | Forward Voltage | $V_F$ | | $I_F$ = 1 mA | | 300 | | mV |
| 3 | Δ Forward Voltage | $\Delta V_F$ | | $I_F$ = 1 mA | | | 20 | mV |
| 4 | Total Capacitance | $C_T$ | | $V_R$ = 0 V<br>$F^R$ = 1 MHz | | | .35 | pF |
| 5 | Δ Total Capacitance | $\Delta C_T$ | | $V_R$ = 0 V<br>$F^R$ = 1 MHz | | | .1 | pF |
| 6 | Serial Resistance | $R_S$ | | $\frac{Vf(10mA)-Vf(1mA)}{9}$ | | 15 | | Ω |
| 7 | Noise figure | NF | LO = +3dBm 9.3GHz<br>$I_F$ = 30MHz , 1.5dB NF | | | | 6.5 | dB |